



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

35
Amdt H
D. Smalls-Logan
1-2803

In re the Application of:)
)
NISHIMOTO et al) Art Unit: 2823
)
Serial No.: 08/897,839) Examiner: K. Eaton
)
Filed: July 21, 1997)
)
For: STRESS-ADJUSTED INSULATING)
FILM FORMING METHOD,)
SEMICONDUCTOR DEVICE AND)
METHOD OF MANUFACTURING THE)
SAME)

RESPONSE TO OFFICE ACTION OF JANUARY 10, 2003

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Responsive to the office action of January 10, 2003, please amend the captioned application as follows:

IN THE CLAIMS:

Please rewrite claim 43 as follows:

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43. (Amended Three Times) A stress-adjusted insulating film forming method for forming a multilayered insulating film on a substrate, said method comprising:

(a) forming a first insulating layer with compressive stress;